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a control gate electrode on the interpoly dielectric.

11. (Withdrawn) The method according to claim 10, comprising:

forming silicon oxide sidewall spacers on the side surfaces of the gate structure;

forming a layer of silicon nitride on an upper surface of the gate stack and on the silicon oxide sidewall spacers; and

thereafter depositing the interlayer dielectric.

12. (Currently Amended) A semiconductor device comprising:

a transistor having a gate structure over a substrate with a gate dielectric layer therebetween;

an interlayer dielectric over the transistor and substrate; and

a silicon-rich silicon oxide layer, having which is substantially opaque to UV radiation and has a refractive index (R.I.) greater than 1.6, on an upper surface of the interlayer dielectric , wherein the silicon-rich silicon oxide layer has a thickness of 400Å to 600Å.

- 13. (Original) The semiconductor device according to claim 12, wherein the siliconrich silicon oxide layer has a R.I. greater than 1.7.
- 14. (Original) The semiconductor device according to claim 13, wherein the siliconrich silicon oxide layer has a R.I. of 1.7 to 2.0.
 - 15. (Cancelled)

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16. (Original) The semiconductor device according to claim 12, wherein the gate structure comprises:

a tunnel oxide as the gate dielectric layer on the substrate;

a floating gate electrode on the tunnel oxide;

an interpoly dielectric comprising an oxide/nitride/oxide (ONO) stack on the floating gate; and

a control gate electrode on the interpoly dielectric.

- 17. (Original) The semiconductor device according to claim 16, comprising silicon oxide sidewall spacers on side surfaces of the gate structure.
- 18. (Original) The semiconductor device according to claim 17, comprising a layer of silicon nitride on an upper surface of the gate structure and on the silicon oxide sidewall spacers.
- 19. (Original) The semiconductor device according to claim 12, wherein the interlayer dielectric comprises a boron-phosphorous-doped silicate glass (BPSG).
 - 20. (Cancelled)